



JCO2 Rec'd PCT/PTO 13 MAY 2002

#5/Re Amended
8-3-02
PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Shin-itsu TAKEHASHI et al.

Group Art Unit:

Serial No.: 10/088,264

Examiner:

Filed: March 18, 2002

For: THIN FILM TRANSISTOR AND METHOD FOR FABRICATING THE SAME

SECOND PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D. C. 20231

Sir:

Prior to examination of the above-identified application,
please amend this application as follows:

IN THE CLAIMS:

Please amend claims 1-54 as follows:

1. (Amended) A method for fabricating an LDD thin film
transistor, comprising:

forming a semiconductor layer on the substrate;

forming a metal film on the semiconductor layer;

PLEASE ACCEPT THIS AS
AUTHORIZATION TO DEBIT
OR CREDIT FEES TO
DEP. ACCT. 16-0331
PARKHURST & WENDEL